ZTX554 Not Recommended for
New Design Please Use ZTX555

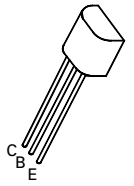
PNP SILICON PLANAR MEDIUM POWER TRANSISTORS

ZTX554
ZTX555

ISSUE 1 – MARCH 94

FEATURES

* 150 Volt V_{CEO}
* 1 Amp continuous current
* P_{tot}= 1 Watt



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	ZTX554	ZTX555	UNIT
Collector-Base Voltage	V_{CBO}	-140	-160	V
Collector-Emitter Voltage	V_{CEO}	-125	-150	V
Emitter-Base Voltage	V_{EBO}	-5		V
Peak Pulse Current	I_{CM}	-2		A
Continuous Collector Current	I_C	-1		A
Power Dissipation: at T_{amb}= 25°C derate above 25°C	P_{tot}	1 5.7		W mW/ °C
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +200		°C

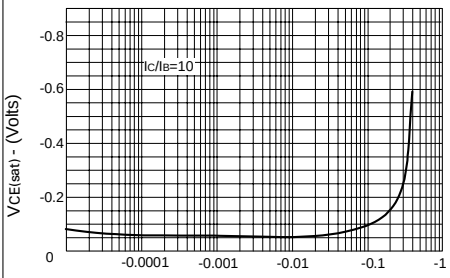
ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	ZTX554		ZTX555		UNIT	CONDITIONS.
		MIN.	MAX	MIN.	MAX		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-140		-160		V	I_C=-100µA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-125		-150		V	I_C=-10mA*
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		-5		V	I_E=-100µA
Collector Cut-Off Current	I_{CBO}		-0.1		-0.1	µA µA	V_{CB}=-120V V_{CB}=-140V
Emitter Cut-Off Current	I_{EBO}		-0.1		-0.1	µA	V_{EB}=-4V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.3		-0.3	V	I_C=-100mA, I_B=-10mA*
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-1		-1	V	I_C=-100mA, I_B=-10mA*
Base-Emitter Turn-on Voltage	$V_{BE(on)}$		-1		-1	V	IC=-100mA, V_{CE}=-10V*
Static Forward Current Transfer Ratio	h_{FE}	50 50	 300	50 50	 300		I_C=-10mA, V_{CE}=-10V* I_C=-300mA, V_{CE}=-10V*
Transition Frequency	f_T	100		100		MHz	I_C=-50mA, V_{CE}=-10V f=100MHz
Output Capacitance	C_{obo}		10		10	pF	V_{CB}=-10V, f=1MHz

ZTX554 Not Recommended for
New Design Please Use ZTX555

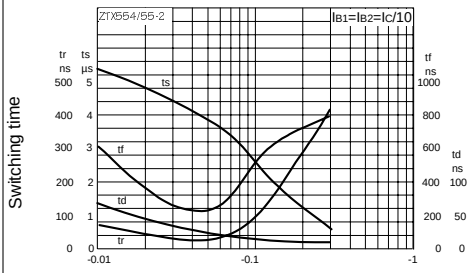
ZTX554
ZTX555

TYPICAL CHARACTERISTICS



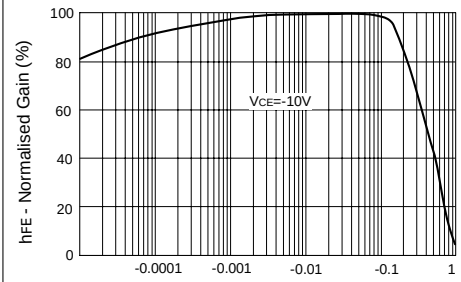
IC - Collector Current (Amps)

VCE(sat) v IC



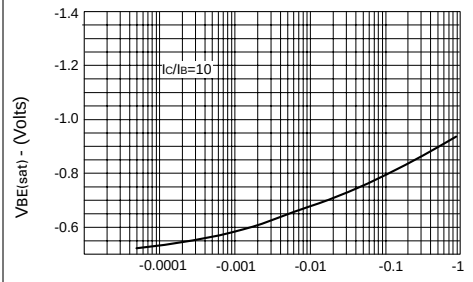
IC - Collector Current (Amps)

Switching Speeds



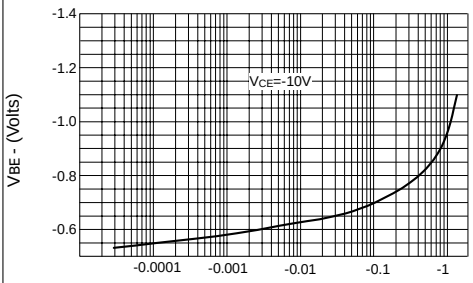
IC - Collector Current (Amps)

hFE v IC



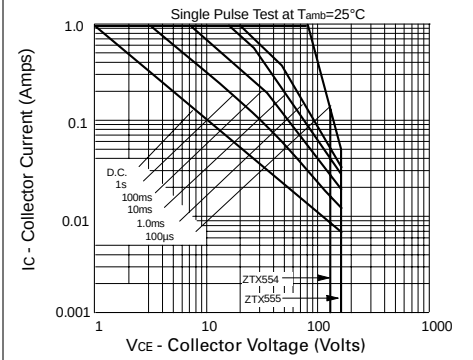
IC - Collector Current (Amps)

VBE(sat) v IC



IC - Collector Current (Amps)

VBE(on) v IC



Safe Operating Area